



2N7002DW

DUAL N-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

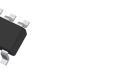
Features

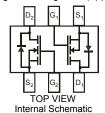
- Dual N-Channel MOSFET
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- Lead Free/RoHS Compliant (Note 2)
- Qualified to AEC-Q101 Standards for High Reliability
- "Green" Device (Note 3 and 4)

Mechanical Data

- Case: SOT-363
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Solderable per MIL-STD-202, Method 208
- Lead Free Plating (Matte Tin Finish annealed over Alloy 42 leadframe).
- Terminal Connections: See Diagram
- Marking Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.006 grams (approximate)

SOT-363





Maximum Ratings @TA = 25°C unless otherwise specified

Characterist	tic	Symbol	Value	Units		
Drain-Source Voltage		V_{DSS}	60	V		
Drain-Gate Voltage $R_{GS} \le 1.0 M\Omega$		V_{DGR}	60	V		
Gate-Source Voltage	Continuous Pulsed	V_{GSS}	±20 ±40	V		
Drain Current (Note 1)	Continuous Continuous @ 100°C Pulsed	I _D	115 73 800	mA		

Thermal Characteristics @TA = 25°C unless otherwise specified

Characteristic	Symbol	Value	Units
Total Power Dissipation Derating above T _A = 25°C (Note 1)	Pd	200 1.60	mW mW/°C
Thermal Resistance, Junction to Ambient	$R_{ hetaJA}$	625	°C/W
Operating and Storage Temperature Range	T _{j,} T _{STG}	-55 to +150	°C

Notes:

- 1. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.
- No purposefully added lead.
- 3. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
- Product manufactured with Date Code UO (week 40, 2007) and newer are built with Green Molding Compound. Product manufactured prior to Date Code UO are built with Non-Green Molding Compound and may contain Halogens or Sb2O3 Fire Retardants.

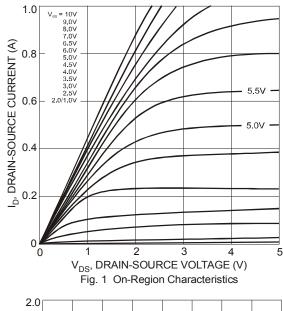


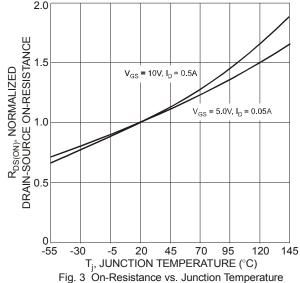
Electrical Characteristics @TA = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 5)							
Drain-Source Breakdown Voltage		BV _{DSS}	60	70		V	$V_{GS} = 0V, I_D = 10\mu A$
Zero Gate Voltage Drain Current	@ $T_C = 25^{\circ}C$ @ $T_C = 125^{\circ}C$	I _{DSS}			1.0 500	μΑ	V _{DS} = 60V, V _{GS} = 0V
Gate-Body Leakage		I _{GSS}		_	±10	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 5)							
Gate Threshold Voltage		V _{GS(th)}	1.0		2.0	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$
Static Drain-Source On-Resistance @ T _i = 25°C				3.2	7.5	Ω	$V_{GS} = 5.0V, I_D = 0.05A$
	@ T _j = 125°C	R _{DS (ON)}		4.4	13.5	5.2	V _{GS} = 10V, I _D = 0.5A
On-State Drain Current		I _{D(ON)}	0.5	1.0	_	Α	V _{GS} = 10V, V _{DS} = 7.5V
Forward Transconductance		g FS	80	_	_	mS	V _{DS} = 10V, I _D = 0.2A
DYNAMIC CHARACTERISTICS							
Input Capacitance		C _{iss}		22	50	рF	
Output Capacitance		Coss		11	25	pF	$V_{DS} = 25V, V_{GS} = 0V, f = 1.0MHz$
Reverse Transfer Capacitance		C _{rss}		2.0	5.0	pF	
SWITCHING CHARACTERISTICS							
Turn-On Delay Time		t _{D(ON)}		7.0	20	ns	$V_{DD} = 30V, I_D = 0.2A, R_L = 150\Omega,$
Turn-Off Delay Time		t _{D(OFF)}	_	11	20	ns	V_{GEN} = 10V, R_{GEN} = 25 Ω

Notes:

5. Short duration pulse test used to minimize self-heating effect.





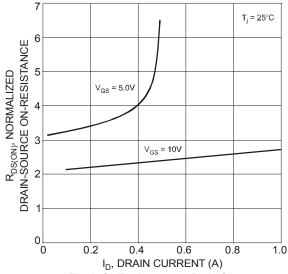


Fig. 2 On-Resistance vs. Drain Current

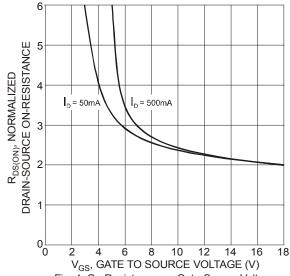


Fig. 4 On-Resistance vs. Gate-Source Voltage

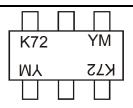


Ordering Information (Note 6)

Part Number	Case	Packaging
2N7002DW-7-F	SOT-363	3000/Tape & Reel

Notes: 6. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information

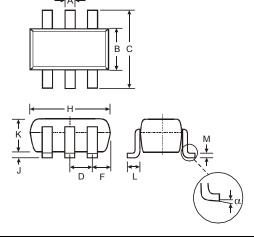


K72 = Product Type Marking Code YM = Date Code Marking Y = Year ex: N = 2002 M = Month ex: 9 = September

Date Code Key

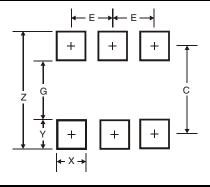
Year	1998	1999	2000	2001	2002	2003	2004	2005	2006	2007	2008	2009	2010	2011	2012
Code	J	K	L	М	N	Р	R	S	Т	U	V	W	Х	Υ	Z
Month	Jan	Fe	b I	Mar	Apr	May	Ju	n	Jul	Aug	Sep	Oc	t I	Nov	Dec
Code	1	2		3	4	5	6		7	8	9	0		N	D

Package Outline Dimensions



SOT-363					
Dim	Min	Max			
Α	0.10	0.30			
В	1.15	1.35			
С	2.00	2.20			
D	0.65 No	ominal			
F	0.30	0.40			
Н	1.80	2.20			
J	_	0.10			
K	0.90	1.00			
L	0.25	0.40			
М	0.10	0.25			
α	0°	8°			
All Dimensions in mm					

Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.5
G	1.3
X	0.42
Y	0.6
С	1.9
Е	0.65

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